

Silicon PNP Power Transistors

2SA985 2SA985A

DESCRIPTION

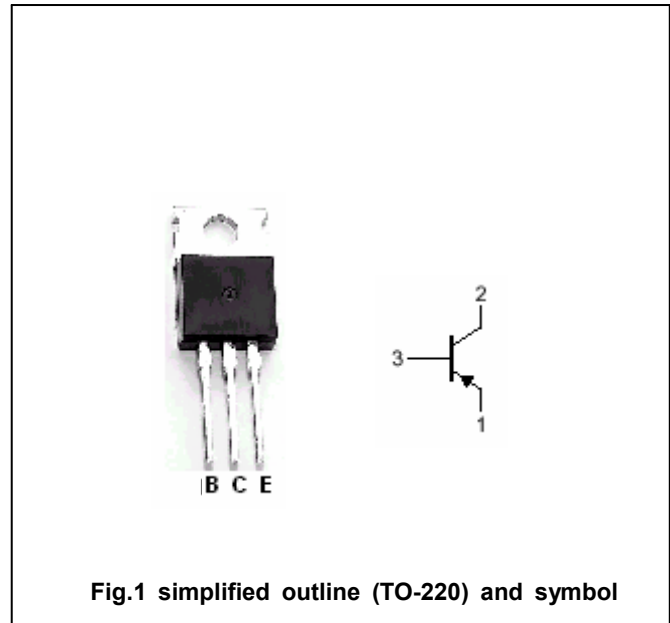
- With TO-220 package
- Complement to type 2SC2275/2275A
- High breakdown voltage

APPLICATIONS

- For low frequency and high frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA985	-120	V
		2SA985A	-150	
V_{CEO}	Collector-emitter voltage	2SA985	-120	V
		2SA985A	-150	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-peak		-3.0	A
I_B	Base current		-0.3	A
P_T	Total power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_c=25^\circ\text{C}$	25	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA985	I _C =-25mA, I _B =0	-120			V
		2SA985A		-150			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-1A; I _B =-0.1A		-0.3	-2.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-1A; I _B =-0.1A		-0.9	-1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =-120V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current		V _{EB} =-3V; I _C =0			-1.0	μA
h _{FE-1}	DC current gain		I _C =-5mA; V _{CE} =-5V	35			
h _{FE-2}	DC current gain		I _C =-0.3A; V _{CE} =-5V	60	150	320	
C _{OB}	Output capacitance		I _E =0; V _{CB} =-10V, f=1MHz		29		pF
f _T	Transition frequency		I _C =-0.2A; V _{CE} =-5V		180		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)